

# **ESD Protection Diode**

# Low Capacitance Array for High Speed Data Lines

# **ESD8006**

The ESD8006 is specifically designed to protect USB 3.0 and Thunderbolt interfaces from ESD. Ultra-low capacitance and low ESD clamping voltage make this device an ideal solution for protecting voltage sensitive high speed data lines. The flow-through style package allows for easy PCB layout and matched trace lengths necessary to maintain consistent impedance between high speed differential lines.

#### **Features**

- Low Capacitance (0.25 pF Max, I/O to GND)
- Protection for the Following IEC Standards: IEC 61000-4-2 (Level 4)
- Low ESD Clamping Voltage
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### **Typical Applications**

- USB 3.0/3.1
- Thunderbolt
- Display Port

# **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	$T_{J}$	-55 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	T <sub>L</sub>	260	°C
IEC 61000-4-2 Contact (ESD) IEC 61000-4-2 Air (ESD)	ESD ESD	±15 ±15	kV kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

See Application Note AND8308/D for further description of survivability specs.

## MARKING DIAGRAM





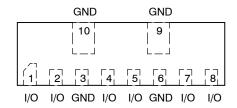
6T = Specific Device Code

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

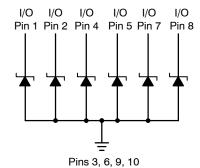
#### **PIN CONFIGURATION**



#### **ORDERING INFORMATION**

Device	Package	Shipping
ESD8006MUTAG	UDFN8 (Pb-Free)	3000 / Tape & Reel
SZESD8006MUTAG	UDFN8 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



Note: Common GND – Only Minimum of 1 GND connection required

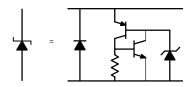
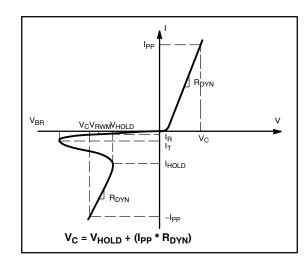


Figure 1. Pin Schematic

# **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter
$V_{RWM}$	Working Peak Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>
Ι <sub>Τ</sub>	Test Current
$V_{HOLD}$	Holding Reverse Voltage
I <sub>HOLD</sub>	Holding Reverse Current
$R_{DYN}$	Dynamic Resistance
I <sub>PP</sub>	Maximum Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ $I_{PP}$ $V_C = V_{HOLD} + (I_{PP} * R_{DYN})$



# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	$V_{RWM}$	I/O Pin to GND			3.3	V
Breakdown Voltage	$V_{BR}$	I <sub>T</sub> = 1 mA, I/O Pin to GND	5.5	7.0		V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 3.3 V, I/O Pin to GND			1.0	μΑ
Holding Reverse Voltage	V <sub>HOLD</sub>	I/O Pin to GND		1.19		V
Holding Reverse Current	I <sub>HOLD</sub>	I/O Pin to GND		25		mA
Clamping Voltage (Note 1)	V <sub>C</sub>	IEC61000-4-2, ±8 KV Contact	See Figures 2 and 3		V	
Clamping Voltage TLP (Note 2) See Figures 6 through 9	V <sub>C</sub>	I <sub>PP</sub> = 8 A I <sub>PP</sub> = -8 A		4.9 -5.0		٧
See Figures 6 tillough 9		I <sub>PP</sub> = 16 A I <sub>PP</sub> = -16 A		8.4 -9.5		
Dynamic Resistance	R <sub>DYN</sub>	I/O Pin to GND 0.44 GND to I/O Pin 0.49			Ω	
Junction Capacitance	С	$V_R$ = 0 V, f = 1 MHz between I/O Pins and GND $V_R$ = 0 V, f = 2.5 GHz between I/O Pins and GND $V_R$ = 0 V, f = 5.0 GHz between I/O Pins and GND $V_R$ = 0 V, f = 1 MHz, between I/O Pins			0.32 0.25 0.25 0.16	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- For test procedure see Figures 4 and 5 and application note AND8307/D.
   ANSI/ESD STM5.5.1 Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions:  $Z_0 = 50 \Omega$ ,  $t_p = 100 \text{ ns}$ ,  $t_r = 4 \text{ ns}$ , averaging window;  $t_1 = 30 \text{ ns}$  to  $t_2 = 60 \text{ ns}$ .

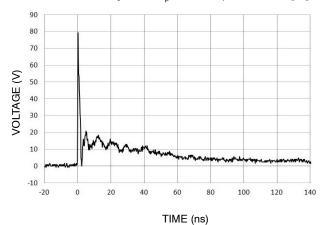
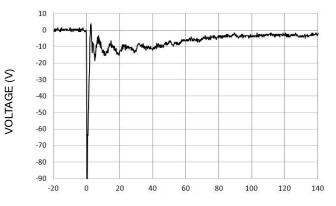


Figure 2. IEC61000-4-2 +8 kV Contact ESD **Clamping Voltage** 



TIME (ns) Figure 3. IEC61000-4-2 -8 kV Contact **Clamping Voltage** 

# IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

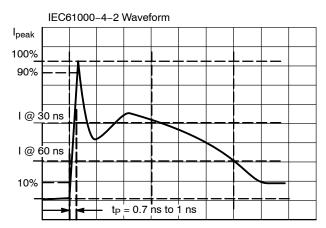
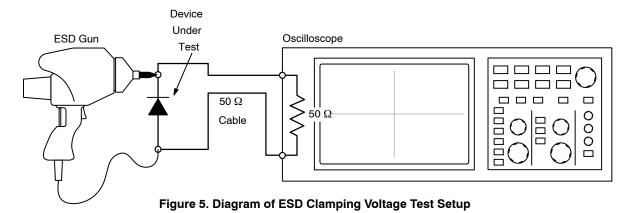


Figure 4. IEC61000-4-2 Spec

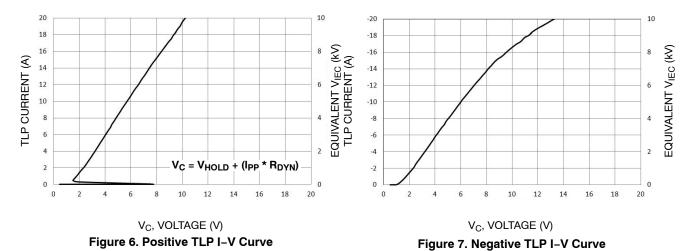


The following is taken from Application Note AND8307/D – Characterization of ESD Clamping Performance.

### **ESD Voltage Clamping**

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. **onsemi** has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how **onsemi** creates these screenshots and how to interpret them please refer to AND8307/D and AND8308/D.



NOTE: TLP parameter: Z<sub>0</sub> = 50 Ω, t<sub>p</sub> = 100 ns, t<sub>r</sub> = 300 ps, averaging window: t<sub>1</sub> = 30 ns to t<sub>2</sub> = 60 ns. V<sub>IEC</sub> is the equivalent voltage stress level calculated at the secondary peak of the IEC 61000–4–2 waveform at t = 30 ns with 2 A/kV. See TLP description below for more information.

# Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 8. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 9 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels. For more information on TLP measurements and how to interpret them please refer to AND9007/D.

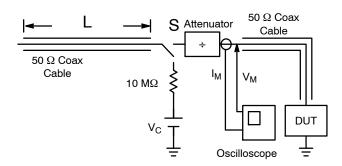


Figure 8. Simplified Schematic of a Typical TLP System

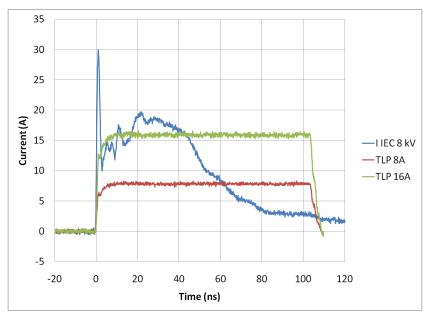


Figure 9. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

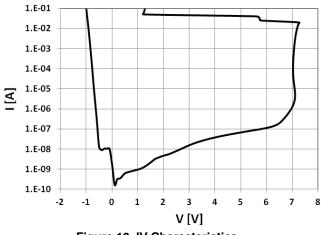


Figure 10. IV Characteristics

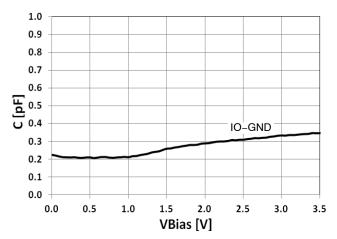


Figure 11. CV Characteristics

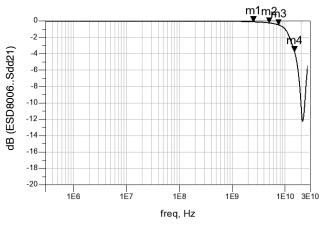


Figure 12. RF Insertion Loss

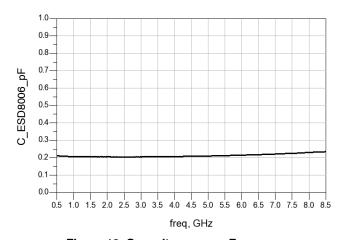


Figure 13. Capacitance over Frequency

Table 1. RF INSERTION LOSS: APPLICATION DESCRIPTION

Interface	Data Rate (Gb/s)	Fundamental Frequency (GHz)	3 <sup>rd</sup> Harmonic Frequency (GHz)	ESD8006 Insertion Loss (dB)
USB 3.0	5.0	2.5 (m1)	7.5 (m3)	m1 = 0.098 m2 = 0.240
Thunderbolt, USB 3.1	10	5.0 (m2)	15 (m4)	m3 = 0.479 m4 = 3.732

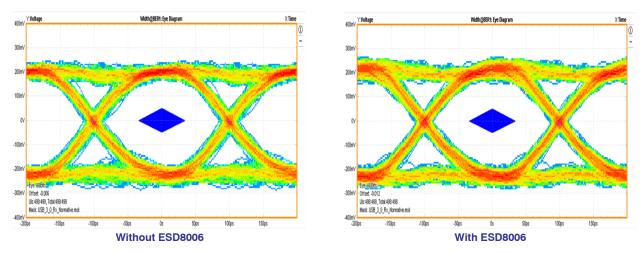


Figure 14. USB 3.0 Eye Diagram with and without ESD8006. 5 Gb/s

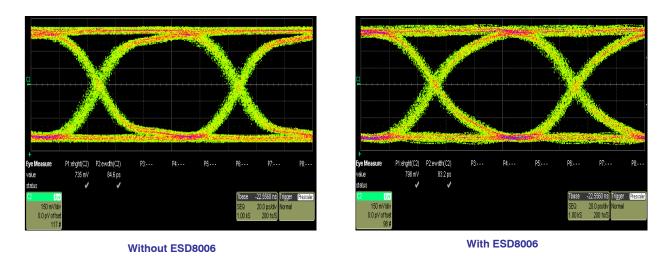


Figure 15. Thunderbolt and USB 3.1 Eye Diagram with and without ESD8006. 10 Gb/s

See application note AND9075/D for further description of eye diagram testing methodology.

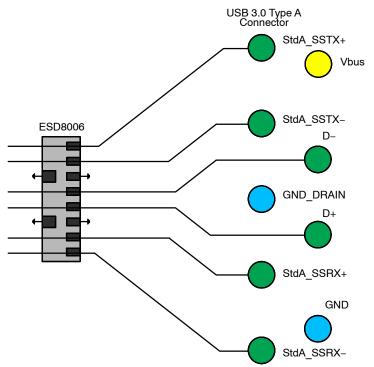
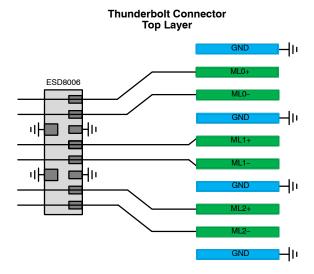


Figure 16. USB 3.0/3.1 Layout Diagram



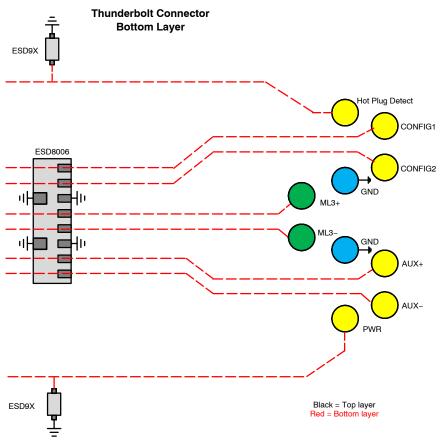


Figure 17. Thunderbolt Layout Diagram

### **PCB Layout Guidelines**

Steps must be taken for proper placement and signal trace routing of the ESD protection device in order to ensure the maximum ESD survivability and signal integrity for the application. Such steps are listed below.

- Place the ESD protection device as close as possible to the I/O connector to reduce the ESD path to ground and improve the protection performance.
  - ◆ In USB 3.0 applications, the ESD protection device should be placed between the AC coupling capacitors and the I/O connector on the TX differential lanes as shown in Figure 18. In this configuration, no DC current can flow through the ESD protection device preventing any potential

- latch-up condition. For more information on latchup considerations, see below description on Page 11.
- Make sure to use differential design methodology and impedance matching of all high speed signal traces.
  - Use curved traces when possible to avoid unwanted reflections.
  - Keep the trace lengths equal between the positive and negative lines of the differential data lanes to avoid common mode noise generation and impedance mismatch.
  - Place grounds between high speed pairs and keep as much distance between pairs as possible to reduce crosstalk.

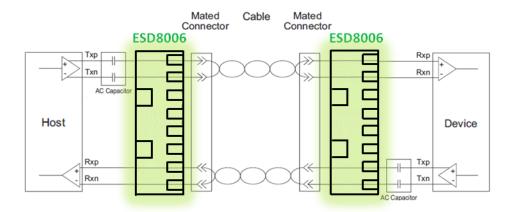


Figure 18. USB 3.0 Connection Diagram

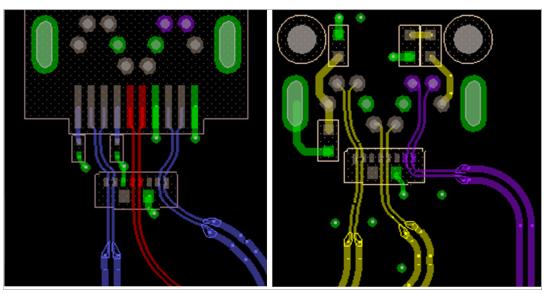


Figure 19. Thunderbolt Recommended PCB Layout

### Latch-Up Considerations

onsemi's 8000 series of ESD protection devices utilize a snap-back, SCR type structure. By using this technology, the potential for a latch-up condition was taken into account by performing load line analysis of common high speed serial interfaces. Example load lines for latch-up free applications and applications with the potential for latch-up are shown below with a generic IV characteristic of a snapback, SCR type structured device overlaid on each. In the latch-up free load line case, the IV characteristic of the snapback protection device intersects the load-line in one unique point ( $V_{\rm OP}$ ,  $I_{\rm OP}$ ). This is the only stable operating point of the circuit and the system is therefore latch-up free.

Please note that for USB 3.0 applications, ESD8006 latch-up free considerations are explained in more detail in the above PCB layout guidelines. In the non-latch up free load line case, the IV characteristic of the snapback protection device intersects the load-line in two points (Vopa, Iopa) and (Vopb, Iopb). Therefore in this case, the potential for latch-up exists if the system settles at (Vopb, Iopb) after a transient. Because of this, ESD8006 should not be used for HDMI applications – ESD8104 or ESD8040 have been designed to be acceptable for HDMI applications without latch-up. Please refer to Application Note AND9116/D for a more in-depth explanation of latch-up considerations using ESD8000 series devices.

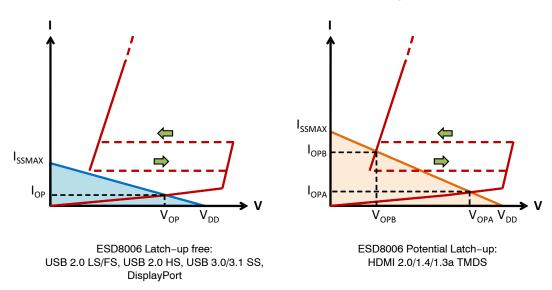
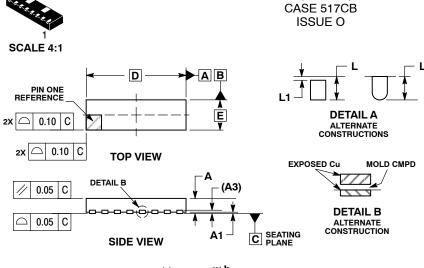


Figure 20. Example Load Lines for Latch-up Free Applications and Applications with the Potential for Latch-up

Table 2. SUMMARY OF SCR REQUIREMENTS FOR LATCH-UP FREE APPLICATIONS

Application	VBR (min) (V)	IH (min) (mA)	VH (min) (V)	onsemi ESD8000 Series Recommended PN
HDMI 2.0/1.4/1.3a TMDS	3.465	54.78	1.0	ESD8104, ESD8040
USB 2.0 LS/FS	3.301	1.76	1.0	ESD8004
USB 2.0 HS	0.482	N/A	1.0	ESD8004
USB 3.0/3.1 SS	2.800	N/A	1.0	ESD8004, ESD8006
DisplayPort	3.600	25.00	1.0	ESD8004, ESD8006





0.10 M C A B

0.05 M C NOTE 3

0.10 M C A B

0.05 M

# **RECOMMENDED SOLDERING FOOTPRINT\***

**BOTTOM VIEW** 

<-- 2X D2

Ф

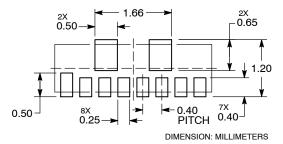
e/2

G2

е

DETAIL A

2X E2



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# UDFN8, 3.3x1.0, 0.4P

DATE 27 SEP 2011

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. DIMENSION 6 APPLIES TO PLATED TERMINAL AND 1S MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
А3	0.13	REF		
b	0.15	0.25		
D	3.30 BSC			
D2	0.25	0.45		
E	1.00 BSC			
E2	0.45 0.5			
е	0.40 BSC			
G2	1.19 BSC			
L	0.20	0.30		
L1		0.15		
12	0.30	0.40		

# **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON59259E	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	UDFN8, 3.3X1.0, 0.4P		PAGE 1 OF 1

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries, onsemi reserves brisefin and of 160 m are trademarked to demonstrate the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

ESD8006MUTAG SZESD8006MUTAG